

# **isc Silicon NPN Power Transistor**

# BUX47A

# DESCRIPTION

- Collector-Emitter Sustaining Voltage-: V<sub>CEO(SUS)</sub>= 450V (Min)
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## **APPLICATIONS**

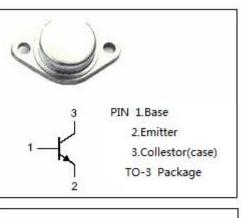
Designed for high voltage, fast switching applications.

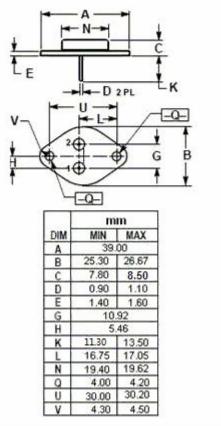
### Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT				
VCER	Collector-Emitter Voltage ( $R_{BE}$ = 10 $\Omega$ )	1000	V				
V <sub>CES</sub>	Collector-Emitter Voltage (V <sub>BE</sub> = 0)	900	V				
$V_{\text{CEO}}$	Collector-Emitter Voltage	450	V				
V <sub>EBO</sub>	Emitter-Base Voltage	7	V				
I <sub>C</sub>	Collector Current-Continuous	9	А				
I <sub>CM</sub>	Collector Current-Peak tp< 5ms	15	А				
IB	Base Current-Continuous	8	А				
I <sub>BM</sub>	Base Current-peak t <sub>p</sub> < 5ms	10	А				
Pc	Collector Power Dissipation @T <sub>c</sub> =25°C	125	W				
Tj	Junction Temperature	175	°C				
T <sub>stg</sub>	Storage Temperature Range	-65~175	°C				

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.2	°C/W







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# **ELECTRICAL CHARACTERISTICS**

## $T_{c}\text{=}25^{\circ}\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> =50mA; I <sub>B</sub> = 0	450		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 50mA; I <sub>C</sub> = 0	7	30	V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5Α; I <sub>B</sub> = 1Α		1.5	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 8A; I <sub>B</sub> = 2.5A		3.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1A		1.6	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> =850V; I <sub>E</sub> = 0 V <sub>CB</sub> =850V; I <sub>E</sub> = 0; T <sub>C</sub> =125℃		0.15 1.5	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0		1.0	mA



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